

# RJH60D3DPE

Silicon N Channel IGBT Application: Inverter

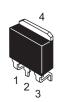
REJ03G1844-0100 Rev.1.00 Oct 14, 2009

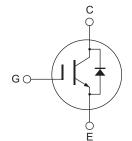
# **Features**

- High breakdown-voltage
- Low on-voltage
- Built-in diode

# **Outline**

RENESAS Package code: PRSS0004AE-B (Package name: LDPAK (S)-(1) )





- 1. Gate
- 2. Collector
- 3. Emitter
- 4. Collecotor

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

	Item	Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V <sub>CES</sub> / V <sub>R</sub>	600	V
Gate to emitter voltage		V <sub>GES</sub>	±30	V
Collector peak current	Tc = 25°C	Ic	30	А
	Tc = 100°C	Ic	15	Α
Collector peak current		ic(peak) Note1	60	А
Collector to emitter diode forward current		i <sub>DF</sub>	15	Α
Collector to emitter diode forward peak current		i <sub>DF</sub> (peak) Note1	60	Α
Collector dissipation		P <sub>C</sub> Note2	120	W
Junction to case thermal impedance		θj-c Note2	1.04	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

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# **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I <sub>CES</sub> / I <sub>R</sub>	_	_	100	μА	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0
Gate to emitter leak current	I <sub>GES</sub>	_	_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	_	6.0	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.6	2.2	V	I <sub>C</sub> = 15 A, V <sub>GE</sub> = 15 V <sup>Note3</sup>
	V <sub>CE(sat)</sub>	_	1.8	_	V	$I_C = 30A$ , $V_{GE} = 15 V^{Note3}$
Input capacitance	Cies	_	900	_	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	50	_	pF	V <sub>GE</sub> = 0
Reveres transfer capacitance	Cres		30	_	pF	f = 1 MHz
Total gate charge	Qg		35	_	nC	V <sub>GE</sub> = 15 V
Gate to emitter charge	Qge		7	_	nC	V <sub>CE</sub> = 300 V
Gate to collector charge	Qgc	_	20	_	nC	I <sub>C</sub> = 15 A
Switching time	t <sub>d(on)</sub>	_	40	_	ns	I <sub>C</sub> = 15 A
	t <sub>r</sub>	_	45	_	ns	$R_L = 20 \Omega$
	t <sub>d(off)</sub>	_	60	_	ns	V <sub>GE</sub> = 15 V
	t <sub>f</sub>	_	100	_	ns	Rg = 5 Ω
EDD Forward voltage	\/_		1.0	2.2	V	I <sub>F</sub> = 15 A <sup>Note3</sup>
FRD Forward voltage	$V_{F}$	_	1.8	2.3	V	I <sub>F</sub> = 15 A

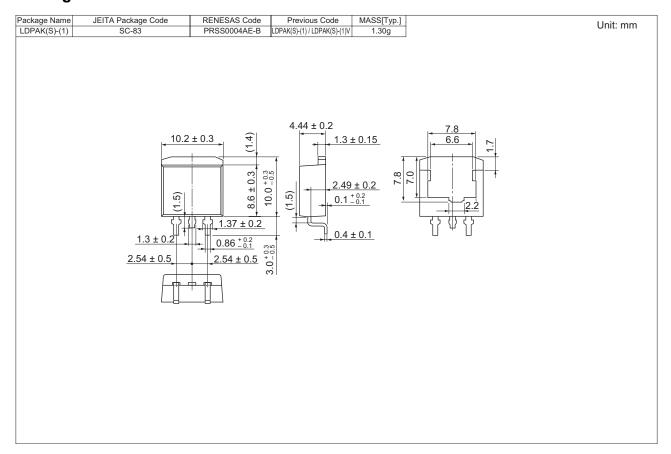
FRD Forward voltage	$V_{F}$	_	1.8	2.3	V	I <sub>F</sub> = 15 A <sup>Note3</sup>
FRD reverse recovery time	t <sub>rr</sub>	_	100	_	ns	I <sub>F</sub> = 15 A
						di <sub>F</sub> /dt = 100 A/μs

Notes: 3. Pulse test.

4. Under development  $\,$  — The specifications potentially be changed without notice.

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# **Package Dimension**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJH60D3DPE-00-J3	1000 pcs	Taping

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